

Hussein Nili

List of Publications by Year in descending order

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Version: 2024-02-01

40
papers

3,461
citations

331259

21
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377514

34
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42
all docs

42
docs citations

42
times ranked

6237
citing authors

#	ARTICLE	IF	CITATIONS
1	Elemental Analogues of Graphene: Silicene, Germanene, Stanene, and Phosphorene. <i>Small</i> , 2015, 11, 640-652.	5.2	725
2	Two-Dimensional Molybdenum Trioxide and Dichalcogenides. <i>Advanced Functional Materials</i> , 2013, 23, 3952-3970.	7.8	443
3	Flexible metasurfaces and metamaterials: A review of materials and fabrication processes at micro- and nano-scales. <i>Applied Physics Reviews</i> , 2015, 2, 011303.	5.5	303
4	Transition metal oxides – Thermoelectric properties. <i>Progress in Materials Science</i> , 2013, 58, 1443-1489.	16.0	302
5	Implementation of multilayer perceptron network with highly uniform passive memristive crossbar circuits. <i>Nature Communications</i> , 2018, 9, 2331.	5.8	281
6	High-Performance Field Effect Transistors Using Electronic Inks of 2D Molybdenum Oxide Nanoflakes. <i>Advanced Functional Materials</i> , 2016, 26, 91-100.	7.8	164
7	Spike-timing-dependent plasticity learning of coincidence detection with passively integrated memristive circuits. <i>Nature Communications</i> , 2018, 9, 5311.	5.8	153
8	Hardware-intrinsic security primitives enabled by analogue state and nonlinear conductance variations in integrated memristors. <i>Nature Electronics</i> , 2018, 1, 197-202.	13.1	148
9	Nanoscale Resistive Switching in Amorphous Perovskite Oxide (SrTiO_3) Memristors. <i>Advanced Functional Materials</i> , 2014, 24, 6741-6750.	7.8	111
10	4K-memristor analog-grade passive crossbar circuit. <i>Nature Communications</i> , 2021, 12, 5198.	5.8	97
11	In situ nanoindentation: Probing nanoscale multifunctionality. <i>Progress in Materials Science</i> , 2013, 58, 1-29.	16.0	90
12	Donor-Induced Performance Tuning of Amorphous SrTiO_3 Memristive Nanodevices: Multistate Resistive Switching and Mechanical Tunability. <i>Advanced Functional Materials</i> , 2015, 25, 3172-3182.	7.8	68
13	Transparent functional oxide stretchable electronics: micro-tectonics enabled high strain electrodes. <i>NPG Asia Materials</i> , 2013, 5, e62-e62.	3.8	67
14	Stretchable and Tunable Microtectonic ZnO-Based Sensors and Photonics. <i>Small</i> , 2015, 11, 4532-4539.	5.2	54
15	Acoustic-Excitonic Coupling for Dynamic Photoluminescence Manipulation of Quasi-2D MoS_2 Nanoflakes. <i>Advanced Optical Materials</i> , 2015, 3, 888-894.	3.6	39
16	Microstructure and dynamics of vacancy-induced nanofilamentary switching network in donor doped SrTiO_3 memristors. <i>Nanotechnology</i> , 2016, 27, 505210.	1.3	39
17	Reset-voltage-dependent precise tuning operation of $\text{TiOx}/\text{Al}_2\text{O}_3$ memristive crossbar array. <i>Applied Physics Letters</i> , 2020, 117, .	1.5	35
18	An Ultrasensitive Silicon Photonic Ion Sensor Enabled by 2D Plasmonic Molybdenum Oxide. <i>Small</i> , 2019, 15, e1805251.	5.2	31

#	ARTICLE	IF	CITATIONS
19	Reduced impurity-driven defect states in anodized nanoporous Nb ₂ O ₅ : the possibility of improving performance of photoanodes. <i>Chemical Communications</i> , 2013, 49, 6349.	2.2	28
20	Alkali ratio control for lead-free piezoelectric thin films utilizing elemental diffusivities in RF plasma. <i>CrystEngComm</i> , 2013, 15, 7222.	1.3	26
21	A Physical Unclonable Function With Redox-Based Nanoionic Resistive Memory. <i>IEEE Transactions on Information Forensics and Security</i> , 2018, 13, 437-448.	4.5	24
22	Mixed-Signal Neuromorphic Inference Accelerators: Recent Results and Future Prospects. , 2018, , .		21
23	Nano-Intrinsic True Random Number Generation: A Device to Data Study. <i>IEEE Transactions on Circuits and Systems I: Regular Papers</i> , 2019, 66, 2615-2626.	3.5	19
24	Comprehensive Compact Phenomenological Modeling of Integrated Metal-Oxide Memristors. <i>IEEE Nanotechnology Magazine</i> , 2020, 19, 344-349.	1.1	19
25	Correlation between nanomechanical and piezoelectric properties of thin films: An experimental and finite element study. <i>Materials Letters</i> , 2013, 90, 148-151.	1.3	18
26	Transparent amorphous strontium titanate resistive memories with transient photo-response. <i>Nanoscale</i> , 2017, 9, 14690-14702.	2.8	18
27	RX-PUF: Low Power, Dense, Reliable, and Resilient Physically Unclonable Functions Based on Analog Passive RRAM Crossbar Arrays. , 2018, , .		16
28	Conduction mechanism effect on physical unclonable function using Al ₂ O ₃ /TiO _x memristors. <i>Chaos, Solitons and Fractals</i> , 2021, 152, 111388.	2.5	15
29	Nanoscale electro-mechanical dynamics of nano-crystalline platinum thin films: An <i>in situ</i> electrical nanoindentation study. <i>Journal of Applied Physics</i> , 2014, 116, .	1.1	13
30	Intrinsic Bounds for Computing Precision in Memristor-Based Vector-by-Matrix Multipliers. <i>IEEE Nanotechnology Magazine</i> , 2020, 19, 429-435.	1.1	13
31	Ultra-Low Power Physical Unclonable Function with Nonlinear Fixed-Resistance Crossbar Circuits. , 2019, , .		11
32	Towards the Development of Analog Neuromorphic Chip Prototype with 2.4M Integrated Memristors. , 2019, , .		10
33	Combinatorial optimization by weight annealing in memristive hopfield networks. <i>Scientific Reports</i> , 2021, 11, 16383.	1.6	10
34	ChipSecure. , 2019, , .		9
35	3D ReRAM arrays and crossbars: Fabrication, characterization and applications. , 2017, , .		8
36	A Strong Physically Unclonable Function With 2.3×10^{-9} CRPs and $<1.4\%$ BER Using Passive ReRAM Technology. <i>IEEE Solid-State Circuits Letters</i> , 2020, 3, 182-185.	1.3	8

#	ARTICLE	IF	CITATIONS
37	Semiconductors: Two-Dimensional Molybdenum Trioxide and Dichalcogenides (Adv. Funct. Mater.) Tj ETQq1 1 0.784314 rgBT /Over	7.8	6
38	Predictive Analysis of 3D ReRAM-Based PUF for Securing the Internet of Things. , 2018, , .		4
39	Utilizing I-V non-linearity and analog state variations in ReRAM-based security primitives. , 2017, , .		3
40	The Impact of Device Uniformity on Functionality of Analog Passively-Integrated Memristive Circuits. IEEE Transactions on Circuits and Systems I: Regular Papers, 2021, 68, 4090-4101.	3.5	3